

November 2013

FDP090N10

N-Channel PowerTrench[®] MOSFET 100 V, 75 A, 9 m Ω

Features

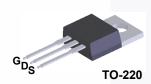
- $R_{DS(on)}$ = 7.2 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(\text{on})}$
- · High Power and Current Handling Capability
- · RoHS Compliant

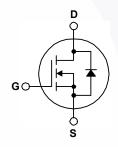
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micor Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDP090N10	Unit
V_{DSS}	Drain to Source Voltage	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage	Gate to Source Voltage		±20	V
I _D	Drain Current	- Continuous (T _C = 85°C)		75	Α
I _{DM}	Drain Current	- Pulsed (No	ote 1)	300	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		ote 2)	309	mJ
I _{AR}	Avalanche Current (Note 1)		ote 1)	75	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		ote 1)	20.8	mJ
dv/dt	Peak Diode Recovery dv/c	it (N	ote 3)	5.6	V/ns
Б	Dawer Dissipation	$(T_C = 25^{\circ}C)$		208	W
P_{D}	Power Dissipation	- Derate Above 25°C		1.39	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C
TL	Maximum Lead Temperatu	ure for Soldering, 1/8" from Case for 5 Second	s	300	°C

Thermal Characteristics

Symbol	Parameter FDP090N10			
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 0.72		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		- C/VV	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP090N10	FDP090N10	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Parameter Test Conditions		Тур.	Max.	Unit
Off Charac	cteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	100	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	^
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	ı	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.5	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$	1	7.2	9	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 37.5 A	-	100	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	_	6185	8225	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	585	775	pF
C _{rss}	Reverse Transfer Capacitance	1 111112	-	235	355	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			-	107	224	ns
t _r	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_{D} = 75 \text{ A},$		-	322	655	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{G} = 25 Ω		-	166	342	ns
t _f	Turn-Off Fall Time		(Note 4)	-	149	309	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 50 V, I _D = 75 A,		-	89	116	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V		-	37	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	22	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		/ -	-	75	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 75 A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 75 A,	-	73	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	166	-	nC

- 1: Repetitive rating: pulse-width limited by maximum junction temperature.
- 2: L = 0.11 mH, I_{AS} = 75 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3: I_{SD} \leq 75 A, di/dt \leq 200 A/ μ s, V_{DD} \leq BV $_{DSS}$, starting T_{J} = 25°C.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

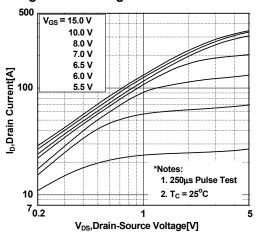


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

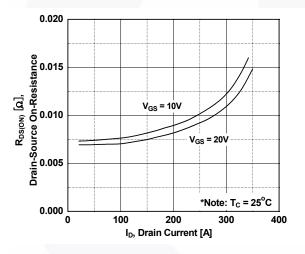


Figure 5. Capacitance Characteristics

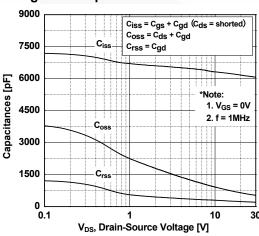


Figure 2. Transfer Characteristics

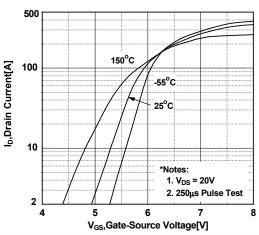


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

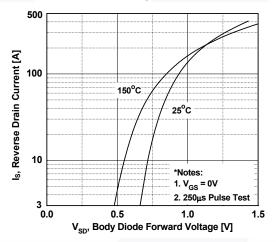
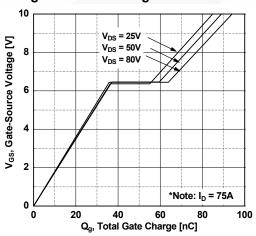


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

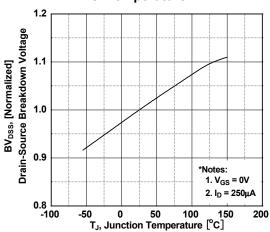


Figure 8. On-Resistance Variation vs. Temperature

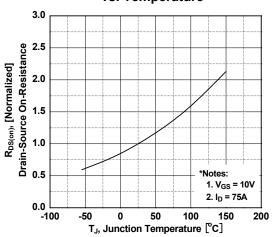


Figure 9. Maximum Safe Operating Area

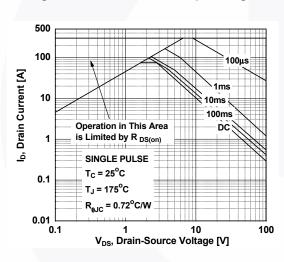


Figure 10. Maximum Drain Current vs. Case Temperature

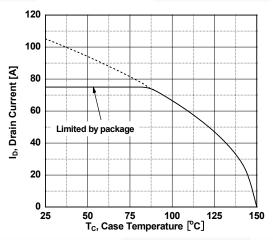
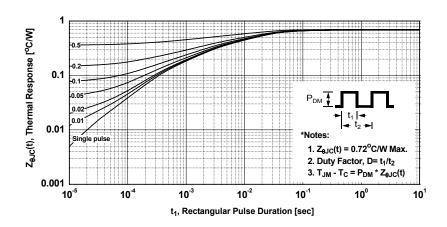


Figure 11. Transient Thermal Response Curve



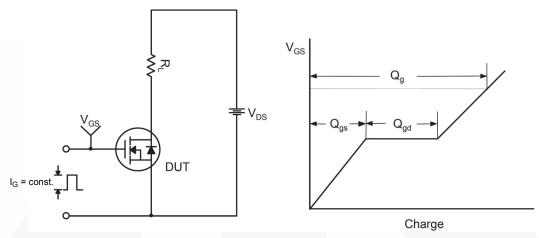


Figure 12. Gate Charge Test Circuit & Waveform

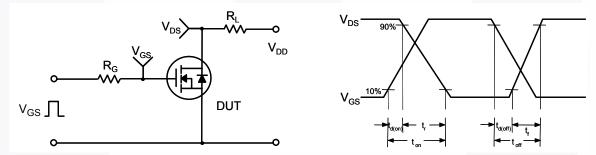


Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

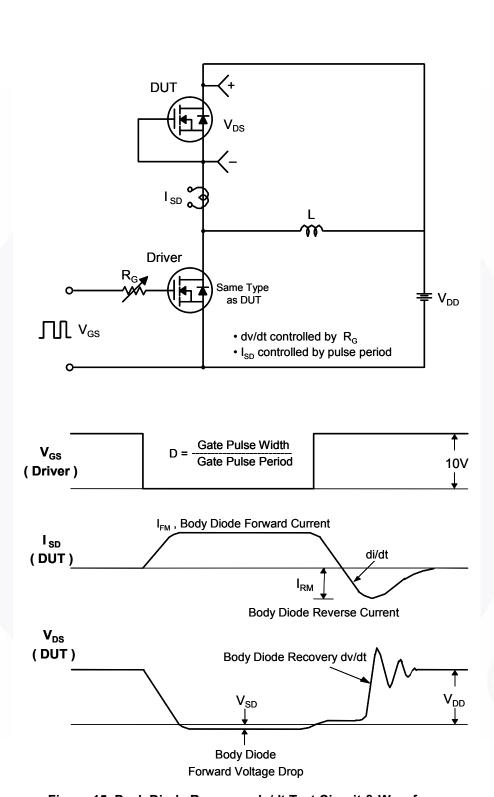


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

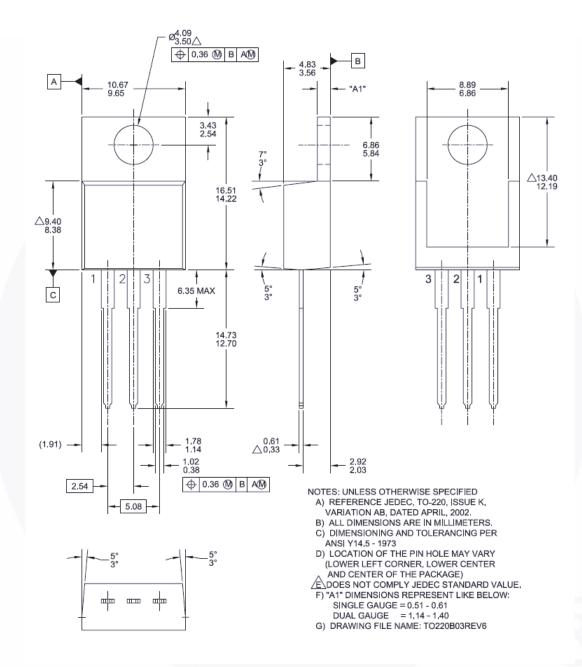


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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